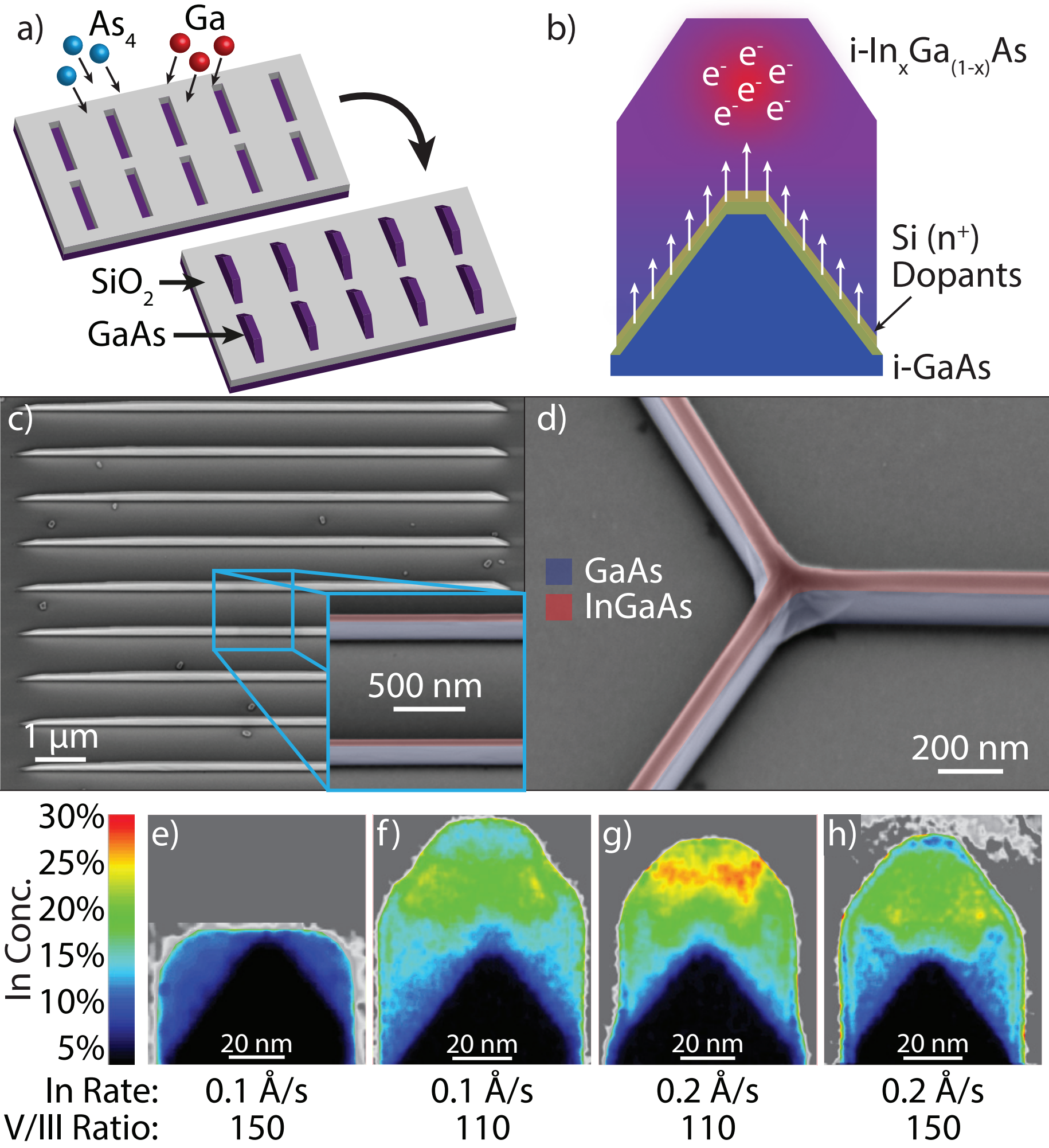
a)
As4
Ga
SiO2
GaAs
b)
i-InxGa(1-x)As
e-
Si (n+)
Dopants
i-GaAs
c)
500 nm
1 µm
d)
GaAs
InGaAs
200 nm
30%
25%
20%
15%
10%
5%
In Conc.
e)
f)
g)
h)
20 nm
In Rate: 0.1 Å/s 0.1 Å/s 0.2 Å/s 0.2 Å/s
V/III Ratio: 150 110 110 150